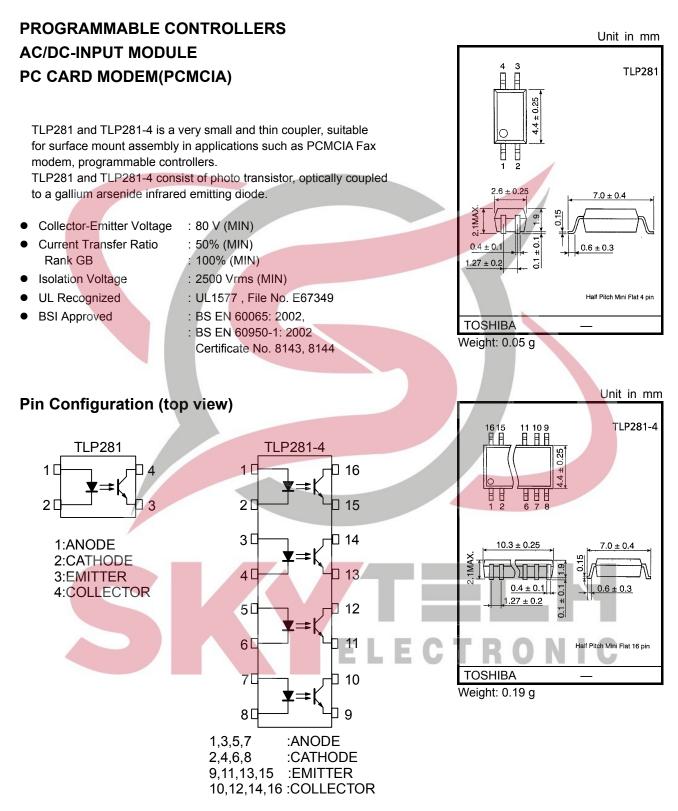
TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

# TLP281,TLP281-4



2007-10-01

1

TYPE	Classi- Fication(*1)	(I <sub>C</sub>	fer Ration (%) / I <sub>F</sub> ) = 5 V, Ta = 25°C Max	Marking of Classification
	Blank	50	600	Blank ,Y <sup>■</sup> ,YE,G,G <sup>■</sup> ,GR,B,BL,GB
	Rank Y	50	150	YE
	Rank GR	100	300	GR
	Rank BL	200	600	BL
TLP281	Rank GB	100	600	GB
	Rank YH	75	150	Y
	Rank GRL	100	200	G
	Rank GRH	150	300	G
	Rank BLL	200	400	В
TLP281-4	Blank	50	600	Blank , GB
167201-4	Rank GB	100	600	GB

\*1: Ex. rank GB: TLP281 (GB)

(Note): Application type name for certification test, please use standard product type name, i.e.

TLP281 (GB): TLP281–1 , TLP281–4 (GB): TLP281–4



Absolute Maximum Ratings (Ta = 25°C)

$\begin{tabular}{ c c c c c c } \hline CHARACTERISTIC & SYMBOL & RATING & UNIT \\ \hline TLP281 & TLP281-4 & UNIT \\ \hline Forward Current & IF & 50 & mA \\ \hline Forward Current Derating & $\Delta I_F / ^{\circ}C$ & -0.7 (Ta $$> 53 ^{\circ}C$) & -0.5 (Ta $$> 25 ^{\circ}C$) \\ \hline Pulse Forward Current & IFP & 1 & A \\ \hline Reverse Voltage & V_R & 5 & V \\ \hline Junction Temperature & T_j & 125 & ^{\circ}C \\ \hline Collector-Emitter Voltage & V_{CEO} & 80 & V \\ \hline Emitter-Collector Voltage & V_{ECO} & 7 & V \\ \hline Collector Current & I_C & 50 & mA \\ \hline Collector Power Dissipation & P_C & 150 & 100 & mW \\ \hline Collector Power Dissipation & P_C & 150 & 100 & mW / ^{\circ}C \\ \hline Junction Temperature & T_j & 125 & ^{\circ}C \\ \hline Operating (Ta $$> 25 ^{\circ}C$) (1 Circuit) & $$\Delta P_C / ^{\circ}C$ & -1.5 & -1.0 & mW / ^{\circ}C \\ \hline Storage Temperature Range & T_{stg} & -55 - 125 & ^{\circ}C \\ \hline Lead Soldering Temperature & T_{sol} & 260 (10s) & ^{\circ}C \\ \hline Total Package Power Dissipation & P_T & 200 & 170 & mW \\ \hline \end{tabular}$		•	•				
$\begin{tabular}{ c c c c c c c } \hline TLP281 & TLP281-4 \\ \hline TLP281 & TLP281-4 \\ \hline TLP281 & TLP281-4 \\ \hline TLP281-4 & TLP281-4 \\ \hline TLP281 & TLP281-4 & TLP28-4 & TLP28-4$		CHARACTERISTIC	SYMBOL	RAT	UNIT		
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$		of which be had been as	OTMBOE	TLP281	TLP281-4	CINIT	
$\begin{array}{c c c c c c c c c c c c c c c c c c c $		Forward Current	١ <sub>F</sub>	5	0	mA	
Reverse Voltage $V_R$ 5 $V$ Junction Temperature $T_j$ 125°CJunction Temperature $T_j$ 125°CCollector-Emitter Voltage $V_{CEO}$ 80 $V$ Emitter-Collector Voltage $V_{ECO}$ 7 $V$ Collector CurrentIc50mACollector Power Dissipation (1 Circuit)Pc150100Collector Power Dissipation Derating(Ta≥25°C) (1 Circuit) $\Delta Pc$ /°C-1.5-1.0Junction Temperature $T_j$ 125°COperating Temperature RangeTopr-55~100°CStorage Temperature Range $T_{sol}$ 260 (10s)°CTotal Package Power Dissipation Package Power DissipationPr200170mW/		Forward Current Derating	∆l <sub>F</sub> /°C	−0.7 (Ta≥53°C)	−0.5 (Ta≥25°C)	mA /°C	
Interfore Fortage $T_{K}$ $C$ Junction Temperature $T_{j}$ 125°CJunction Temperature $T_{j}$ 125°CCollector-Emitter Voltage $V_{CEO}$ 80 $V$ Emitter-Collector Voltage $V_{ECO}$ 7 $V$ Collector CurrentIC50mACollector Power Dissipation (1 Circuit)Pc150100Collector Power Dissipation Derating(Ta≥25°C) (1 Circuit) $\Delta Pc$ /°C $-1.5$ $-1.0$ Junction Temperature $T_{j}$ 125°COperating Temperature Range $T_{opr}$ $-55~100$ °CStorage Temperature Range $T_{stg}$ $-55~125$ °CLead Soldering Temperature $T_{sol}$ 260 (10s)°CTotal Package Power Dissipation $P_T$ 200170mW/	LED	Pulse Forward Current	I <sub>FP</sub>		1	А	
$\frac{1}{10} = \frac{1}{10} $		Reverse Voltage	V <sub>R</sub>	Ę	5	V	
$\frac{1}{100} = \frac{1}{1000} = \frac{1}$	Junction Temperature		Tj	12	25	°C	
$\begin{array}{c c c c c c c c c c c c c c c c c c c $		Collector-Emitter Voltage	V <sub>CEO</sub>	8	0	V	
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$		Emitter-Collector Voltage	V <sub>ECO</sub>	7	7	V	
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	OR	Collector Current	Ι <sub>C</sub>	50		mA	
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	ETECT		Pc	150	100	mW	
Operating Temperature Range     Topr     -55~100     °C       Storage Temperature Range     Tstg     -55~125     °C       Lead Soldering Temperature     Tsol     260 (10s)     °C       Total Package Power Dissipation     Pr     200     170     mW(	DE		ΔP <sub>C</sub> /°C	-1.5	-1.0	mW /°C	
Storage Temperature Range     Tstg     -55~125     °C       Lead Soldering Temperature     Tsol     260 (10s)     °C       Total Package Power Dissipation     PT     200     170     mW/		Junction Temperature	Тј	12	25	°C	
Lead Soldering Temperature     Tsol     260 (10s)     °C       Total Package Power Dissipation     PT     200     170     mW/	Ope	era <mark>ting Te</mark> mperature Range	Topr	-55-	~100	°C	
Total Package Power Dissipation PT 200 170 mW	Sto	rage Temperature Range	T <sub>stg</sub>	-55-	~125	°C	
	Lea	d Soldering Temperature	T <sub>sol</sub>	260	(10s)	°C	
			PT	200	170	mW	
Total Package Power Dissipation Derating (Ta≥25°C) (1 Circuit)∆PT /°C−2.0−1.7mW /°C			∆P <sub>T</sub> /°C	-2.0	-1.7	mW /°C	
Isolation Voltage (Note1) BV <sub>S</sub> 2500(AC,1min,R.H.≤60%) Vrms	Isol	ation Voltage (Note1)	BVS	2500(AC,1mi	n,R.H.≤60%)	Vrms	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### Individual Electrical Characteristics (Ta = 25°C)

	CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
	Forward Voltage		VF	I <sub>F</sub> = 10 mA	1.0	1.15	1.3	V
LED	Reverse Current		IR	V <sub>R</sub> = 5 V	-	_	10	μA
	Capacitance		CT	V = 0, f = 1 MHz	<b>R-O</b>	30	I-C	pF
	Collector-Emitter Breakdown Voltage		V <sub>(BR)</sub> CEO	I <sub>C</sub> = 0.5 mA	80	_	_	v
TOR	Emitter-Collector Breakdown Voltage		V <sub>(BR)</sub> ECO	I <sub>E</sub> = 0.1 mA	7	_	_	v
DETECTOR	Collector Dark Current			V <sub>CE</sub> = 48 V, Ambient Light Below (100 <i>t</i> x)	_	0.01 (2)	0.1 (10)	μA
		(Note2)	ICEO	V <sub>CE</sub> = 48 V, Ta = 85°C Ambient Light Below (100 tx)	_	2 (4)	50 (50)	μA
	Capacitance (Collector to Emitter)		C <sub>CE</sub>	V = 0, f = 1 MHz	_	10	—	pF

(Note 2) Because of the construction,leak current might be increased by ambient light. Please use photocoupler with less ambient light.

<sup>(</sup>Note1) Device considered a two terminal device : LED side pins shorted together and DETECTOR side pins shorted together.

## Coupled Electrical Characteristics (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Transfer Ratio	I <sub>C</sub> / I <sub>F</sub>	I <sub>F</sub> = 5 mA, V <sub>CE</sub> = 5 V	50	_	600	%
	IC / IF	Rank GB	100	_	600	70
Saturated CTR		IF = 1 mA, VCE = 0.4 V	-	60	_	%
Saturated CTR	I <sub>C</sub> / I <sub>F (sat)</sub>	Rank GB	30	_	_	/0
Collector-Emitter		I <sub>C</sub> = 2.4 mA, I <sub>F</sub> = 8 mA	_	_	0.4	
Saturation Voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> = 0.2 mA, I <sub>F</sub> = 1 mA	_	0.2	—	V
Saturation Voltage		Rank GB	_	_	0.4	
Off-State Collector Current	I <sub>C (off)</sub>	V <sub>F</sub> = 0.7 V, V <sub>CE</sub> = 48 V			10	μA

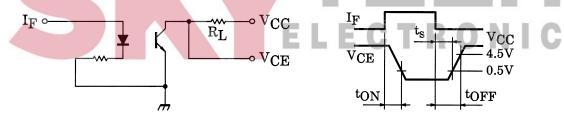
### Isolation Characteristics (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capac <mark>itance</mark> (Input to Output)	CS	V <sub>S</sub> = 0 V, f = 1 MHz	-	0.8	_	pF
Isolation Resistance	R <sub>S</sub>	V <sub>S</sub> = 500 V, R.H.≤60%	5×10 <sup>10</sup>	10 <sup>14</sup>	_	Ω
		AC , 1 minute	2500	_	_	Vrms
Isolation Voltage	BVS	AC, 1 second, in OIL		5000	_	VIIIIS
		DC, 1 minute, in OIL	_	5000	_	Vdc

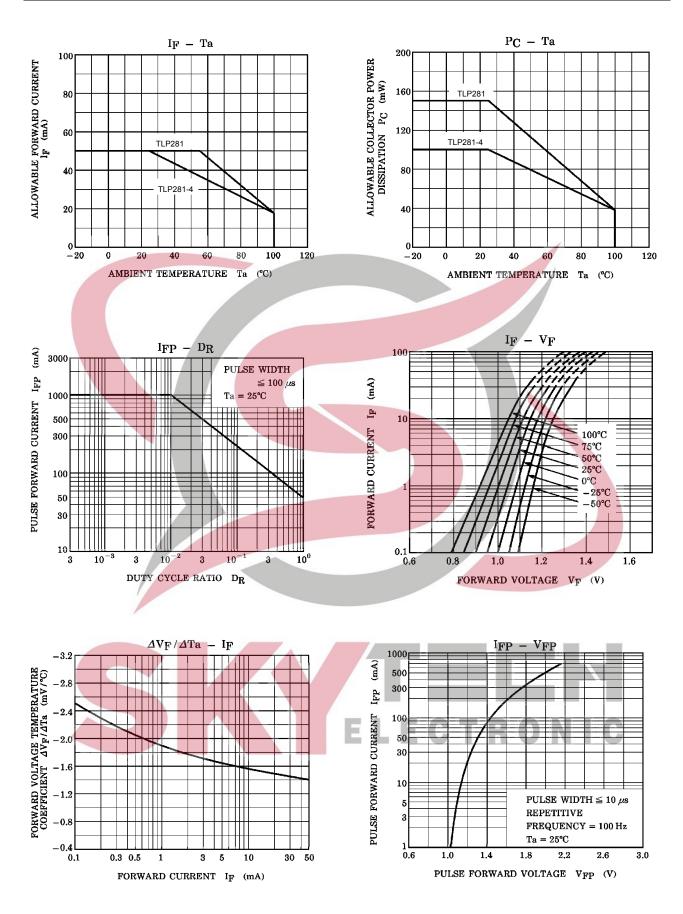
## Switching Characteristics (Ta = 25°C)

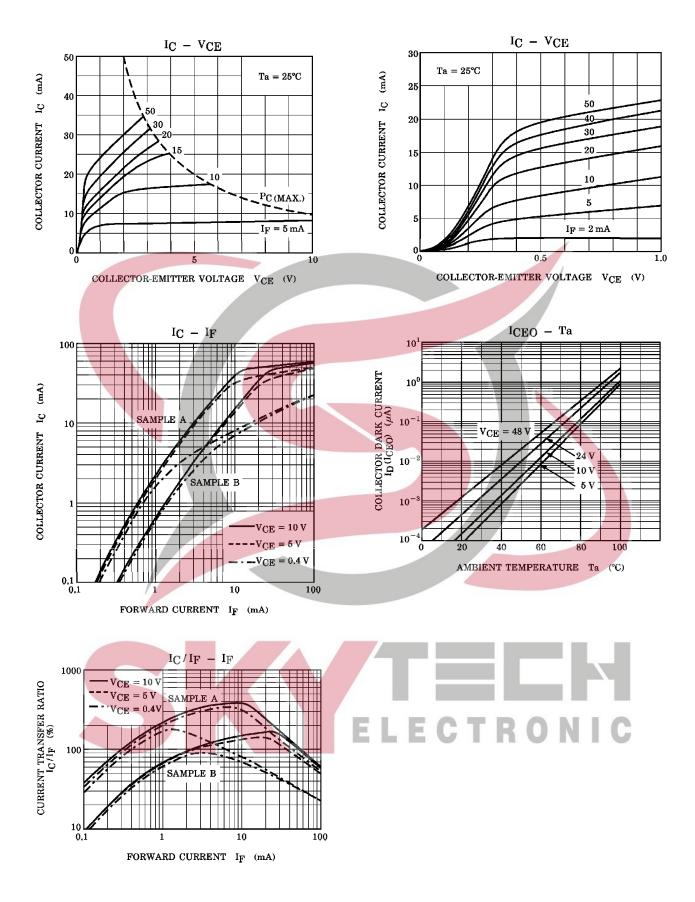
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Rise Time	tr		_	2	_	
Fall Time	t <sub>f</sub>	$V_{CC} = 10 \text{ V}, \text{ I}_{C} = 2 \text{ mA}$ $R_{L} = 100\Omega$		3	_	μs
Turn-On Time	t <sub>on</sub>		_	3		
Turn-Off Time	toff			3	—	
Turn-On Time	t <sub>ON</sub>		_	2	—	
Storage Time	ts	R <sub>L</sub> = 1.9 kΩ (Fig.1) V <sub>CC</sub> = 5 V, I <sub>F</sub> = 16 mA	_	25	_	μs
Turn-Off Time	tOFF		_	40	_	

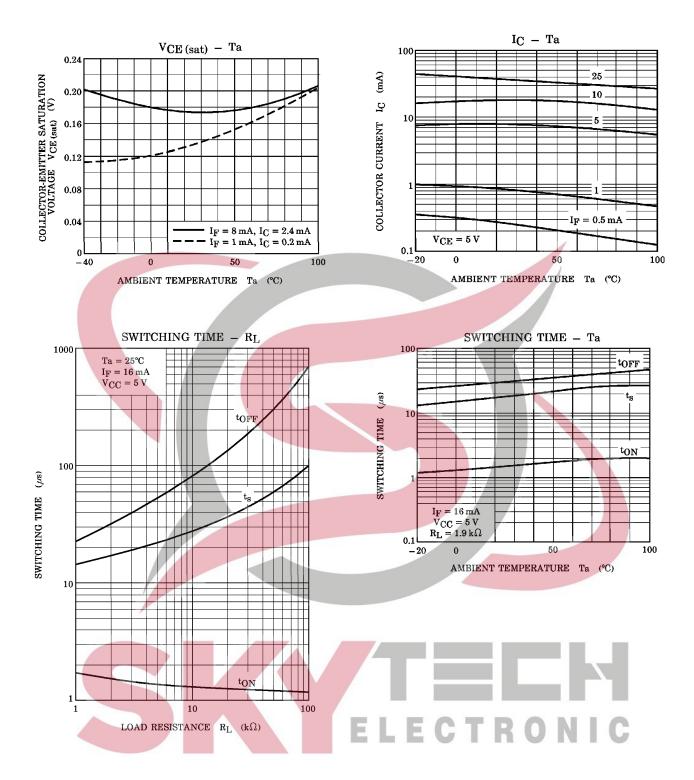
(Fig.1)SWITCHING TIME TEST CIRCUIT



2007-10-01







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20070701-EN

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